

## Publication List

Atsushi Oshiyama

## (A) Original Papers

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13. A. Natori, T. Ohno and A. Oshiyama, "Work Function of Alkali-Atom Adsorbed Graphite", *J. Phys. Soc. Jpn.* **54** (1985) 3042-3050.
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15. N. Hamada, S. Ohnishi and A. Oshiyama, "Energy-Bands and Stable Structures of Ultra-Thin-Layer Semiconductor Superlattices", *Proc. 18-th Int. Conf. Solid State Devices and Materials* ( Tokyo 1986 ) p343-346.
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36. A. Oshiyama and M. Saito, "Diffusion and Aggregation of Oxygen Impurities in Silicon" *Proc. Int. Conf. Defect Control in Semiconductors* ( Yokohama, 1989, Elsevier ) p193-198.

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72. (**plenary**) S. Saito, A. Oshiyama, Y. Miyamoto, N. Hamada and S. Sawada, "Cohesion, Electron States and Superconductivity of Fullerenes and Fullerides", *Proc. 21st Int. Conf. Physics of Semiconductors* (Beijing, 1992, World Scientific) p20-27.
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### (C) Invited Talks

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19. (**Plenary**) A. Oshiyama, “Electronic Structure and Superconductivity of C<sub>60</sub> Fullerides”, *5th Asia-Pacific Physics Conference* (Kuala Lumpur, August 1992).
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#### (E) 受賞

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**(F) 新聞報道**

1. 読売新聞 (2011 年 11 月 18 日): “スパコン「京」に最高栄誉のゴードン・ベル賞”, 朝日新聞 (2011 年 11 月 18 日): “スパコン「京」にゴードン・ベル賞 実計算でも最速証明”, 毎日新聞 (2011 年 11 月 18 日): “スパコン「京」が米国計算機学会のゴードン・ベル賞受賞”, ゴードンベル賞関連は、上記以外に日本経済新聞、産経新聞、日刊工業新聞等に掲載。